Introduction to Electronics

Active Devices



- These are specially made with low (accurate) peak inverse voltages.
- They are used to give a reference voltage

Doping Semiconductors

- The addition of a small percentage of foreign atoms in the regular <u>crystal lattice</u> of silicon or germanium produces dramatic changes in their electrical properties, producing <u>n-type</u> and <u>p-type</u> semiconductors.
- **Pentavalent** impurities (5 <u>valence</u> <u>electrons</u>) produce n-type semiconductors by contributing extra electrons.
- **Trivalent** impurities (3 valence electrons) produce p-type semiconductors by producing a "<u>hole</u>" or electron deficiency.



Boron Aluminum Gallium





Depletion Region

• When a <u>p-n junction</u> is formed, some of the free electrons in the n-region diffuse across the junction and combine with <u>holes</u> to form negative ions. In so doing they leave behind positive ions at the donor <u>impurity</u> sites.



Bipolar Transistor

- A current-controlled valve
 - The current flow from collector to emitter is β
 (a high number) times the base current
 - The base to emitter voltage is 0.7 V when the transistor is on.





Field Effect Transistors

Drain (+ve)

• A voltage-controlled valve



Source (-ve)

